

- ◆ Common Source Push-Pull Pair
- ◆ N-Channel Enhancement Mode
- ◆ Low Q_g and R_g
- ◆ High dv/dt
- ◆ Nanosecond Switching

The DE275X2-102N06A is a matched pair of RF power MOSFET devices in a common source configuration. The device is optimized for push-pull or parallel operation in RF generators and amplifiers at frequencies to >65 MHz.

Unless noted, specifications are for each output device

$$V_{DSS} = 1000 \text{ V}$$

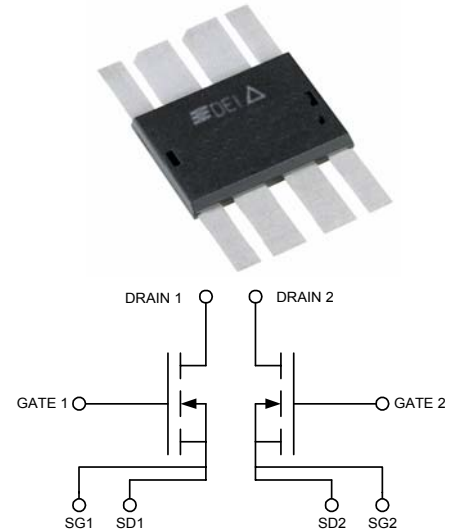
$$I_{D25} = 16 \text{ A}$$

$$R_{DS(on)} = 0.8 \Omega$$

$$P_{DC} = 1180 \text{ W}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_c = 25^\circ\text{C}$	16	A
I_{DM}	$T_c = 25^\circ\text{C}$, pulse width limited by T_{JM}	48	A
I_{AR}	$T_c = 25^\circ\text{C}$	6	A
E_{AR}	$T_c = 25^\circ\text{C}$	20	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 0.2 \Omega$	5	V/ns
	$I_S = 0$	>200	V/ns
$P_{DC}^{(1)}$		1180	W
$P_{DHS}^{(1)}$	$T_c = 25^\circ\text{C}$, Derate $5.0 \text{ W}/^\circ\text{C}$ above 25°C	750	W
$P_{DAMB}^{(1)}$	$T_c = 25^\circ\text{C}$	5.0	W

Symbol	Test Conditions	Characteristic Values		
		$T_J = 25^\circ\text{C}$ unless otherwise specified		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 3 \text{ ma}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ ma}$	2.5		V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = 0.8 V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0$, $T_J = 125^\circ\text{C}$			50 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 15 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2\%$			1.6 Ω
g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 0.5 I_{D25}$, pulse test	2	7.5	S
$R_{thJC}^{(1)}$			0.25	C/W
$R_{thJHS}^{(1)}$			0.50	C/W
T_J		-55		+175 $^\circ\text{C}$
T_{JM}			175	$^\circ\text{C}$
T_{stg}		-55		+175 $^\circ\text{C}$
T_L	1.6mm (0.063 in) from case for 10 s		300	$^\circ\text{C}$
Weight			4	g



Features

- Isolated Substrate
 - high isolation voltage (>2500V)
 - excellent thermal transfer
 - Increased temperature and power cycling capability
- IXYS advanced low Q_g process
- Low gate charge and capacitances
 - easier to drive
 - faster switching
- Low $R_{DS(on)}$
- Very low insertion inductance (<2nH)
- No beryllium oxide (BeO) or other hazardous materials

Advantages

- High Performance Push-Pull RF Package
- Optimized for RF and high speed switching at frequencies to >100MHz
- Easy to mount—no insulators needed
- High power density

Note: All specifications are per each transistor, unless otherwise noted.

⁽¹⁾ Thermal specifications are for the package, not per transistor

Symbol	Test Conditions	Characteristic Values (T _J = 25°C unless otherwise specified)		
		min.	typ.	max.
R _G			0.3	Ω
C _{iss}			1800	pF
C _{oss}	V _{GS} = 0 V, V _{DS} = 0.8 V _{DSS(max)} , f = 1 MHz		130	pF
C _{rss}			25	pF
C _{stray}	Back Metal to any Pin		21	pF
T _{d(on)}			3	ns
T _{on}	V _{GS} = 15 V, V _{DS} = 0.8 V _{DSS} I _D = 0.5 I _{DM}		2	ns
T _{d(off)}	R _G = 0.2 Ω (External)		4	ns
T _{off}			5	ns
Q _{g(on)}			50	nC
Q _{gs}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} I _D = 0.5 I _{D25}		20	nC
Q _{gd}			30	nC

Source-Drain Diode		Characteristic Values (T _J = 25°C unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I _S	V _{GS} = 0 V			6 A
I _{SM}	Repetitive; pulse width limited by T _{JM}			96 A
V _{SD}	I _F = I _S , V _{GS} = 0 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2%			1.5 V
T _{rr}			200	ns
Q _{RM}	I _F = I _S , -di/dt = 100A/μs, V _R = 100V		0.6	μC
I _{RM}			4	A

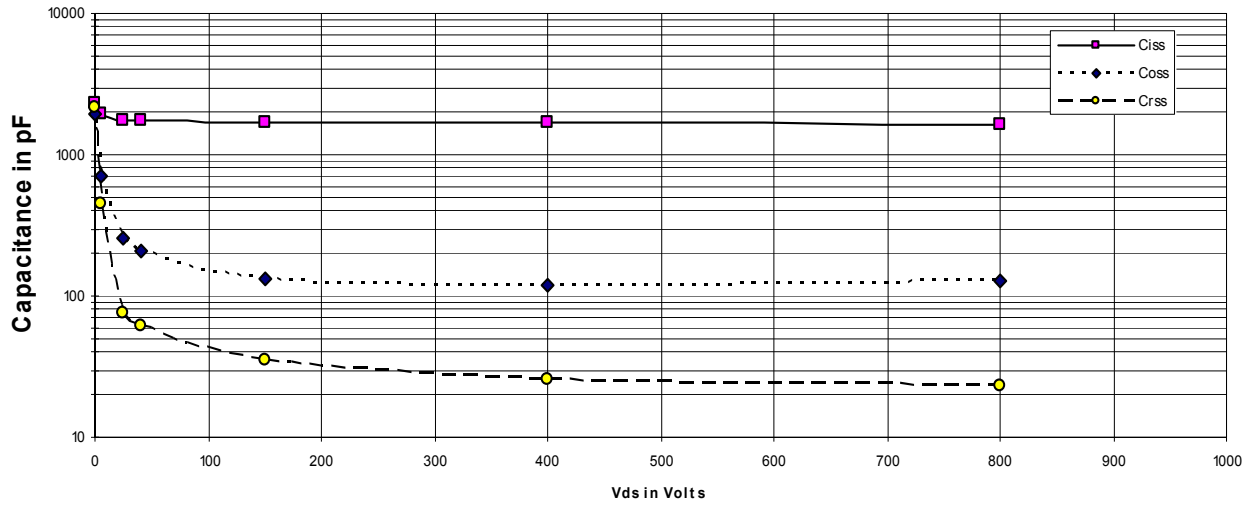
(1) These parameters apply to the package, not individual MOSFET devices.

For detailed device mounting and installation instructions, see the “*DE-Series MOSFET Mounting Instructions*” technical note on IXYS RF’s web site at www.ixysrf.com/Technical_Support/App_notes.html

IXYS RF reserves the right to change limits, test conditions and dimensions.

IXYS RF MOSFETS are covered by one or more of the following U.S. patents:

4,835,592	4,850,072	4,881,106	4,891,686	4,931,844	5,017,508
5,034,796	5,049,961	5,063,307	5,187,117	5,237,481	5,486,715
5,381,025	5,640,045				



275X2-102N06A Capacitances vs Vds

102N06A DE-SERIES SPICE Model

The DE-SERIES SPICE Model is illustrated in Figure 1. The model is an expansion of the SPICE level 3 MOSFET model. It includes the stray inductive terms L_G , L_S and L_D . R_d is the $R_{DS(ON)}$ of the device, R_{ds} is the resistive leakage term. The output capacitance, C_{OSS} , and reverse transfer capacitance, C_{RSS} are modeled with reversed biased diodes. This provides a varactor type response necessary for a high power device model. The turn on delay and the turn off delay are adjusted via R_{on} and R_{off} .

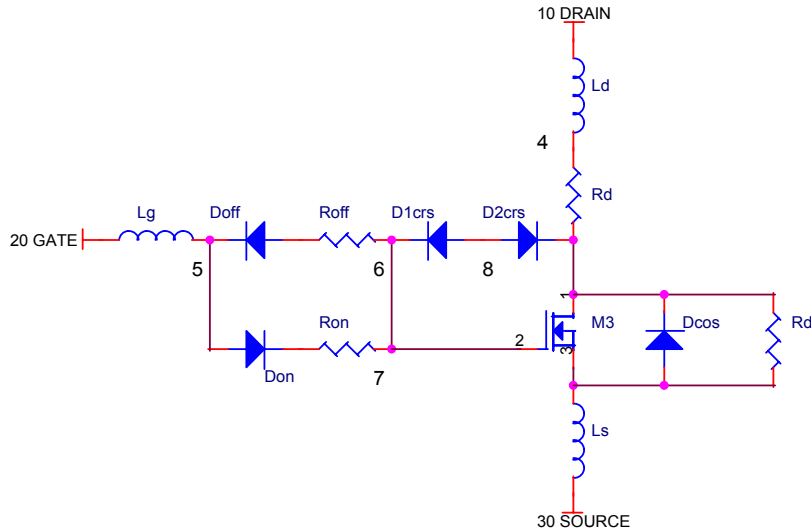


Figure 1 DE-SERIES SPICE Model

This SPICE model may be downloaded as a text file from the DEI web site at www.directedenergy.com/spice.htm

Net List:

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*SYM=POWMOSN
.SUBCKT 102N06A 10 20 30
* TERMINALS: D G S
* 1000 Volt 6 Amp 1.6 Ohm N-Channel Power MOSFET
M1 1 2 3 3 DMOS L=1U W=1U
RON 5 6 .5
DON 6 2 D1
ROF 5 7 1.0
DOF 2 7 D1
D1CRS 2 8 D2
D2CRS 1 8 D2
CGS 2 3 1.9N
RD 4 1 1.6
DCOS 3 1 D3
RDS 1 3 5.0MEG
LS 3 30 .5N
LD 10 4 1N
LG 20 5 1N
.MODEL DMOS NMOS (LEVEL=3 VTO=4 KP=2.3)
.MODEL D1 D (IS=.5F CJO=10P BV=100 M=.5 VJ=.2 TT=1N)
.MODEL D2 D (IS=.5F CJO=400P BV=1000 M=.6 VJ=.6 TT=1N RS=10M)
.MODEL D3 D (IS=.5F CJO=400P BV=1000 M=.35 VJ=.6 TT=400N RS=10M)
.ENDS
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